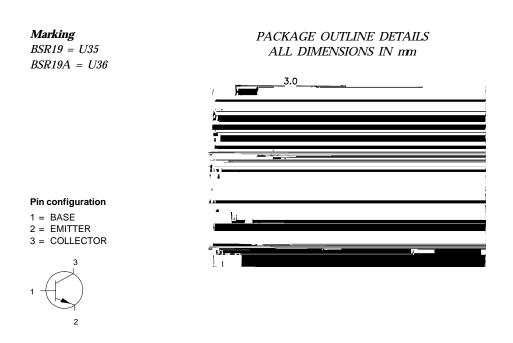


SOT-23 Formed SMD Package

BSR19 BSR19A

# SILICON N-P-N HIGH-VOLTAGE TRANSISTORS

## N-P-N high-voltage small-signal transistors



#### ABSOLUTE MAXIMUM RATINGS

			BSR19 BSR19A		
Collector-base voltage (open emitter)	V <sub>CB0</sub>	max.	160	180	V
Collector-emitter voltage (open base)	$V_{CE0}$	max.	140	160	V
Collector current	$I_C$	max.	600	600	mА
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	P <sub>tot</sub>	max.	250	250	mW
Junction temperature	$T_{j}$	max.	150	150	° C
Collector-emitter saturation voltage	5				
$I_C = 50 mA; l_B = 5 mA$	V <sub>CEsat</sub>	max.	0,25	0,20	V
D.C. current gain					
$I_C = 10 mA; V_{CE} = 5 V$	h <sub>FE</sub>	min.	60	80	

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DATINICE (at T 97% and an attaction and	(G - J)				
<b>RATINGS</b> (at $T_A = 25^{\circ}C$ unless otherwise speci-	nea)				
Limiting values	<b>I</b> /	10	a 1	1.0/	а т <i>и</i>
Collector-base voltage (open emitter)	CDU	ax. 16	-		
Collector-emitter voltage (open base)	CLU	ax. <u>14</u>	-	160	-
Emitter-base voltage (open collector)	LDU	ax.	6		V
Collector current	e	ax.	600		mA
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	101	ax.	250		mW
Junction temperature	T <sub>j</sub> m	ax.	150	)	° C
Storage temperature	Tstg		–55 to	+150	° C
THERMAL RESISTANCE					
From junction to ambient	R <sub>th j-a</sub> =		500	)	K/W
CHARACTERISTICS					
Tarnb = 25 °C unless otherwise specified					
			BSR19	BSR19	<u>A</u>
Collector cut-off current	_				
$I_E = 0; V_{CB} = 100 V$	ICBO	max.	100		nA
$I_E = 0; V_{CB} = 120 V$	I <sub>CBO</sub>	max.		50	nA
$I_E = 0; V_{CB} = 100 V; T_{amb} = 100^{\circ}C$	I <sub>CBO</sub>	max.	100		$\mathfrak{m}A$
$I_E = 0; V_{CB} = 120 V; T_{amb} = 100^{\circ}C$	I <sub>CBO</sub>	max.		50	$\mathfrak{m}A$
Emitter cut-off current					
$I_C = 0; V_{EB} = 4,0 V$	I <sub>EBO</sub>	max.	50	50	nA
Breakdown voltages					
$I_{C}$ : 1,0 mA; $I_{B} = 0$	V(BR) <sub>CEC</sub>	j min.	140	160	V
$I_C = 100 \text{ mA}; I_E = 0$	V(BR) <sub>CBC</sub>	j min.	160	180	V
$I_C = 0; I_E = 10 \text{ mA}$	V(BR) <sub>EBC</sub>	) min.	6,0	6,0	V
Saturation voltages					
$I_C = 10 \text{ mA}; I_B = 1,0 \text{ mA}$	V <sub>CEsat</sub>	max.	0,15	0.15	V
	VBEsat	max.		1,0	V
	· DLSat		_,.	,=	
$I_C = 50 mA; I_B = 5.0 mA$	<b>V</b> CEsat	max.	0,25	0,20	V
	V <sub>BEsat</sub>	max.	1,2	1,0	V
D.C. current gain					
$I_C = 1.0 \text{ mA}; V_{CE} = 5 V$	$h_{FE}$	min.	60	80	
	L		<i>c</i> 0	00	
$I_C = 10 \text{ mA}; V_{CE} = 5 V$	$h_{FE}$	min.	60	80	
		max.	250	250	
$I_C = 50 mA; V_{CE} = 5 V$	$h_{FE}$	min.	20	30	
Small-signal current gain	TTL.		20		
$I_C = 1,0 \text{ mA}; V_{CE} = 10 \text{ V}; f = 1 \text{ kHz}$	h <sub>fe</sub>	min.	50	50	
$I_{U} = 1,0$ IIII $V_{UE} = 10$ $V, I = 1$ IIIZ	шe		200	200	
Output canacitance at $f = 1$ MUz		max.	200	200	
Output capacitance at $f = 1$ MHz	C		0	0	ъF
$I_E = 0; V_{CB} = 10 V$	Co	max.	6	6	pF

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			BSR19 BSR19A		
Input capacitance at $f = 1$ MHz					_
$I_C = 0; V_{EB} = 0.5 V$	Ci	max.	30	30	pF
Transition frequency at $f = 100 \text{ MHz}$					
$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$	$f_T$	min.	100	100	MHz
		max.	300	300	MHz
Noise figure at $R_S = 1 \ k_W$					
$I_C = 250 \text{ mA}; V_{CE} = 5 \text{ V}; f = 10 \text{Hz to } 15,7 \text{ kHz}$	r F	max.	10	8	dB

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